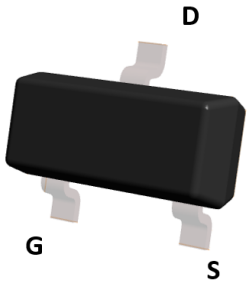
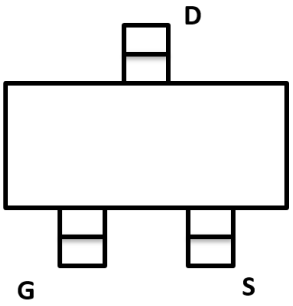
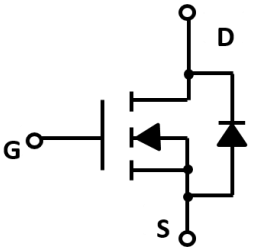
N-Channel Enhancement Mode Field Effect Transistor



Top View





SOT-23

Product Summary

- V_{DS} 50V
- I_D 300mA
- $R_{DS(ON)}$(at V_{GS}=10V) ＜2.5ohm
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜3.0ohm

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface：TTL/CMOS

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	50	V
Gate-source Voltage	V_{GS}	±20	V
Drain Current	I_D	300	mA
Pulsed Drain Current [A]	I_{DM}	1.5	A
Total Power Dissipation @ T_A=25℃	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State [B]	$R_{\theta JA}$	357	℃/ W
Junction and Storage Temperature Range	T_J ,T_{STG}	-55～+150	℃

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	50			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=50V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS1}	V_{GS}= ±20V, V_{DS}=0V			±100	nA
	I_{GSS2}	V_{GS}= ±10V, V_{DS}=0V			±50	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	0.4		1.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=100mA		1.3	2.5	Ω
		V_{GS}= 4.5V, I_D=50mA		1.5	3.0	
Diode Forward Voltage	V_{SD}	I_S=100mA,V_{GS}=0V			1.2	V
Maximum Body-Diode Continuous Current	I_S				100	mA
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V,f=1MHZ		17.5		pF
Output Capacitance	C_{oss}			11.5		
Reverse Transfer Capacitance	C_{rss}			6.5		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=25V,I_D=0.3A		1.7	2.4	nC
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=25V, I_D=300mA, R_{GEN}=6Ω		5		ns
Turn-off Delay Time	$t_{D(off)}$			17		
Reverse recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		ns

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

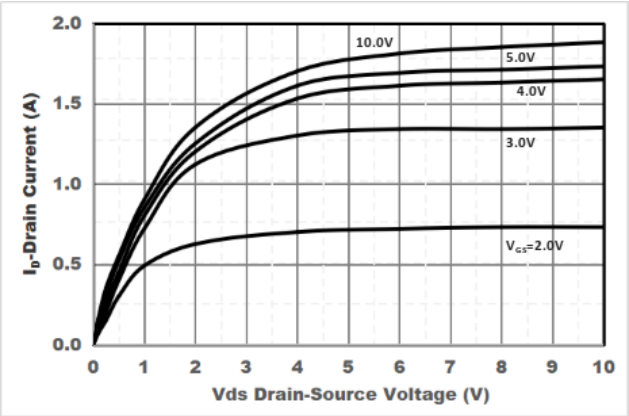


Figure1. Output Characteristics

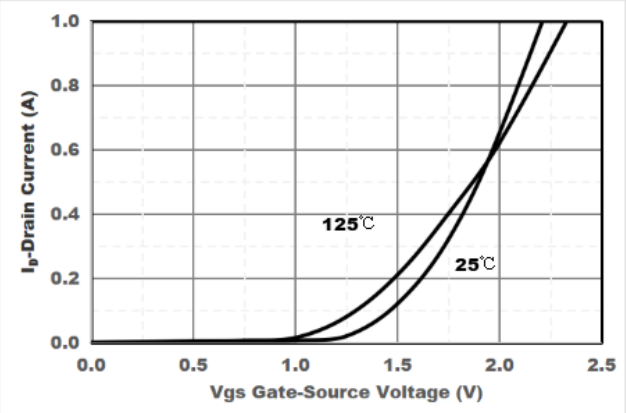


Figure2. Transfer Characteristics

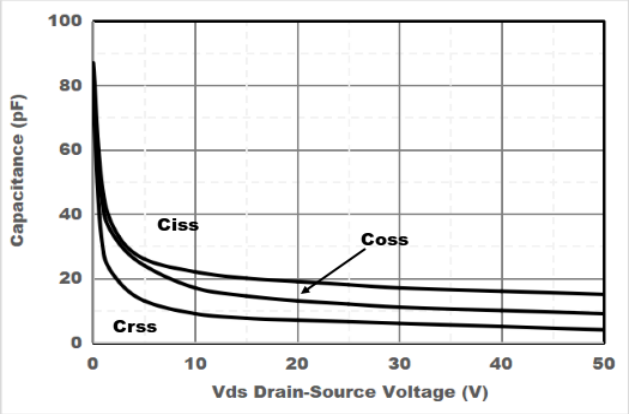


Figure3. Capacitance Characteristics

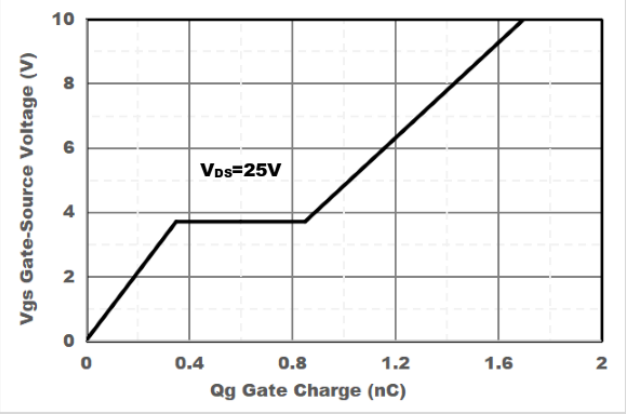


Figure4. Gate Charge

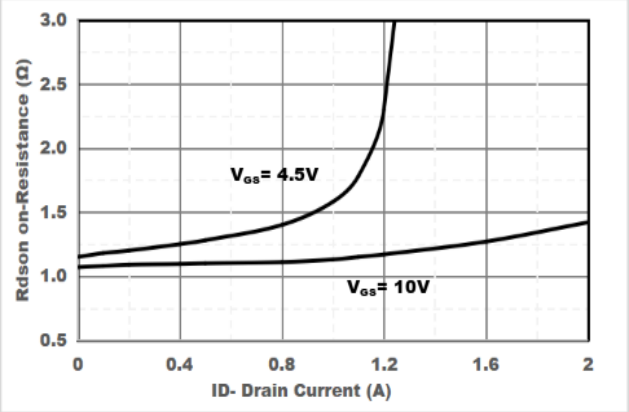


Figure5. Drain-Source on Resistance

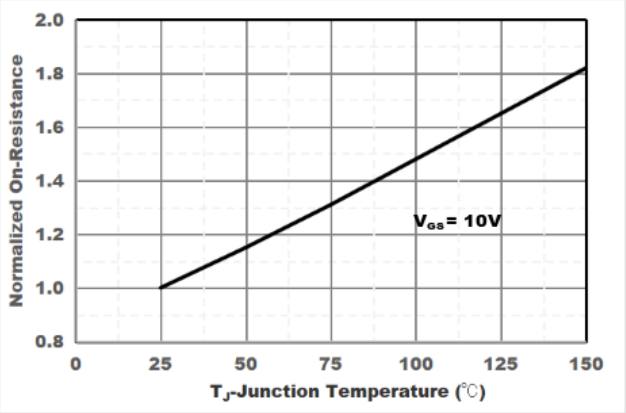


Figure6. Drain-Source on Resistance

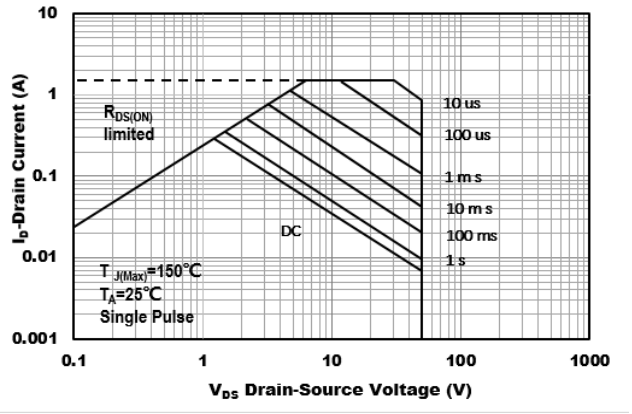


Figure7. Safe Operation Area

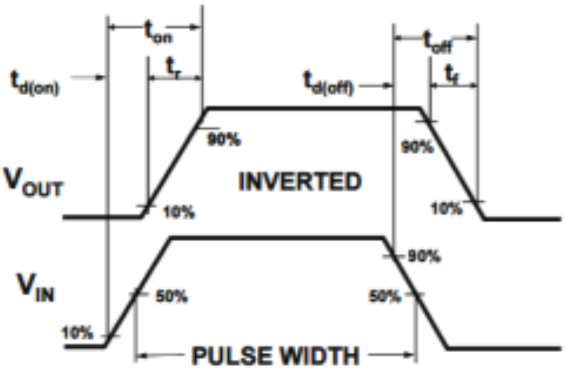
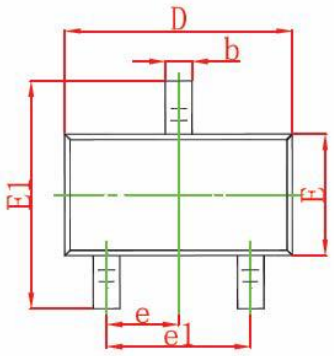
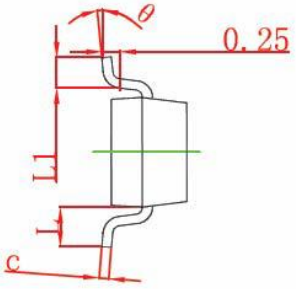
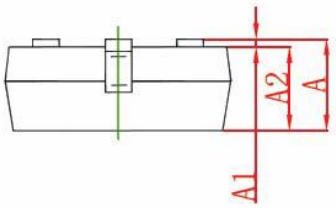


Figure8. Switching wave

■ SOT-23 Package information

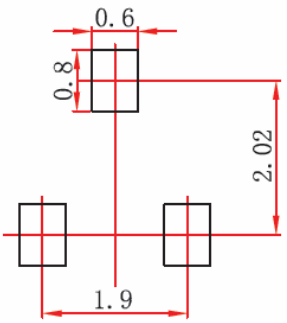






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

■SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.